

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A nanosilicon light-emitting element, wherein comprising:
an amorphous SiO_x film consisting of comprising a mixture of silicon atoms and oxygen atoms is formed on a semiconductor substrate, the result is said amorphous SiO_x film being heat treated in an inert gas to form the silicon atoms into nanosilicon of about 3.0nm or less, and
wherein said amorphous SiO_x film including said nanosilicon the result is treated with an aqueous solution of hydrofluoric acid and subjected to thermal oxidation to allow at least one any of the three primary colors of light to be emitted at a low operating voltage at room temperature.
2. (Currently Amended) A nanosilicon light-emitting element, wherein comprising:
an amorphous SiO_x film consisting of comprising a mixture of silicon atoms and oxygen atoms is formed on a semiconductor substrate, the result is said amorphous SiO_x film being heat treated in an inert gas to form the silicon atoms into nanosilicon of about 3.0nm or less, and
wherein said amorphous SiO_x film including said nanosilicon the result is repeatedly treated with an aqueous solution of hydrofluoric acid and subjected to natural oxidation to allow at least one any of the three primary colors of light to be emitted at a low operating voltage at room temperature.
3. (Currently Amended) The nanosilicon light-emitting element according to claim 1, wherein the a blue color of the three primary colors of light is emitted clearly and in a stable

manner.

4. (Currently Amended) The nanosilicon light-emitting element according to claim 1, wherein the semiconductor substrate is comprises a silicon substrate, and the a temperature of the heat treatment is comprises a temperature in a range of about 900 900°C to 1200°C.

5. (Currently Amended) The nanosilicon light-emitting element according to claim 1, wherein the a temperature of the thermal oxidation treatment is comprises a temperature in a range of about [[400]] 400°C to 1000°C.

6. (Original) The nanosilicon light-emitting element according to claim 1, wherein the nanosilicon is formed by high frequency sputtering.

7. (Currently Amended) A method for manufacturing a nanosilicon light-emitting element, comprising: ~~comprising the steps of:~~
forming an amorphous SiO_x film consisting of comprising a mixture of silicon atoms and oxygen atoms on a semiconductor substrate;
heat treating ~~the result~~ said amorphous SiO_x film in an inert gas to form the silicon atoms into nanosilicon of about 3.0nm or less; and
subjecting said amorphous SiO_x film including said nanosilicon ~~the result~~ to treatment with an aqueous solution of hydrofluoric acid and thermal oxidation to allow at least one any of ~~the~~ three primary colors of light to be emitted at a low operating voltage at room temperature.

8. (Currently Amended) A method for manufacturing a nanosilicon light-emitting

element, comprising: comprising the steps of:

forming an amorphous SiO_x film consisting of comprising a mixture of silicon atoms and oxygen atoms on a semiconductor substrate;

heat treating the result said amorphous SiO_x film in an inert gas to form the silicon atoms into nanosilicon of about 3.0nm or less; and

subjecting said amorphous SiO_x film including said nanosilicon the result repeatedly to treatment with an aqueous solution of hydrofluoric acid and natural oxidation to allow at least one any of the three primary colors of light to be emitted at a low operating voltage at room temperature.

9. (Currently Amended) The method for manufacturing a nanosilicon light-emitting element according to claim 7, wherein the a blue color of the three primary colors of light is emitted clearly and in a stable manner.

10. (Currently Amended) The method for manufacturing a nanosilicon light-emitting element according to claim 7, wherein the semiconductor substrate is comprises a silicon substrate, and the a temperature of the heat treatment is comprises a temperature in a range of about 900 900°C to 1200°C.

11. (Currently Amended) The method for manufacturing a nanosilicon light-emitting element according to claim 7, wherein the a temperature of the thermal oxidation treatment is comprises a temperature in a range of about [[400]] 400°C to 1000°C.

12. (Original) The method for manufacturing a nanosilicon light-emitting element according to claim 7, wherein the nanosilicon is formed by high frequency sputtering.

13. (Currently Amended) The nanosilicon light-emitting element according to claim 2, wherein ~~the a~~ blue color of the three primary colors of light is emitted clearly and in a stable manner.

14. (Currently Amended) The nanosilicon light-emitting element according to claim 2, wherein the semiconductor substrate is comprises a silicon substrate, and ~~the a~~ temperature of the heat treatment is comprises a temperature in a range of about 900 900°C to 1200°C.

15. (Currently Amended) The nanosilicon light-emitting element according to claim 2, wherein ~~the a~~ temperature of the thermal oxidation treatment is comprises a temperature in a range of about [[400]] 400°C to 1000°C.

16. (Original) The nanosilicon light-emitting element according to claim 2, wherein the nanosilicon is formed by high frequency sputtering.

17. (Currently Amended) The method for manufacturing a nanosilicon light-emitting element according to claim 8, wherein ~~the a~~ blue color of the three primary colors of light is emitted clearly and in a stable manner.

18. (Currently Amended) The method for manufacturing a nanosilicon light-emitting element according to claim 8, wherein the semiconductor substrate is comprises a silicon substrate, and ~~the a~~ temperature of the heat treatment is comprises a temperature in a range of about 900 900°C to 1200°C.

19. (Currently Amended) The method for manufacturing a nanosilicon light-emitting

element according to claim 8, wherein the a temperature of the thermal oxidation treatment is comprises a temperature in a range of about [[400]] 400°C to 1000°C.

20. (Original) The method for manufacturing a nanosilicon light-emitting element according to claim 8, wherein the nanosilicon is formed by high frequency sputtering.

21. (New) The nanosilicon light-emitting element according to claim 1, wherein at least a portion of said nanosilicon comprises nanosilicon formed on a surface of said amorphous SiO_x film.

22. (New) A nanosilicon light-emitting element, comprising:
an amorphous SiO_x film formed on a semiconductor substrate, said amorphous SiO_x film comprising nanosilicon formed therein; and
a light emitting layer comprising nanosilicon formed on a surface of said amorphous SiO_x film.

23. (New) The nanosilicon light-emitting element according to claim 22, further comprising:

a transparent electrode formed on said light-emitting layer.

24. (New) The nanosilicon light-emitting element according to claim 23, wherein said light-emitting layer further comprises:
an oxide layer formed on said nanosilicon.

25. (New) The nanosilicon light-emitting element according to claim 22, wherein said

nanosilicon in said light-emitting layer comprises nanosilicon particles having a particle size which is about 3.0 nm or less.